

A B S T R A C T

A method for manufacturing solid electrolytic capacitor that can be mounted direct on a semiconductor component and offers a superior high
5 frequency characteristic. An aluminum foil 20 is provided on one surface with a resist film 23 and then with a through hole 24. Next, an insulation film 25 is formed to cover the other surface of aluminum foil 20 and to fill the first through hole, and then the resist film 23 is removed; and then the surface of aluminum foil 20 is roughened to be provided with a dielectric layer 27
10 thereon. A second through hole 36 is formed in the insulation film 25, which is filling the first through hole 24. A through hole electrode 28 is formed in the second through hole; and then, on the surface of the dielectric layer 27, a solid electrolytic layer 29 and a collector layer 30 are formed. After an opening 37 is provided, a first connection terminal 31 is formed therein, and a
15 second connection electrode 32 on the exposed surface of the through hole electrode 28.



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